



Future Normal in Semiconductor

2025-02-14(금), 09:00-10:45

좌장: 추후업데이트 예정

D. Thin Film Process Technology 분과

[FE1-D] Thin Film Transistors - I

<p>FE1-D-1 09:00-09:15</p>	<p>Innovative Design of Vertically-Stacked IGZO Thin-Film Transistors with Distinctive Planar and Vertical Channels Using a Single Active Layer Ji-Won Kang¹, Yeong-Ha Kwon², Nak-Jin Seong², Kyu-Jeong Choi², Chi-Sun Hwang³, Jong-Heon Yang³, and Sung-Min Yoon¹ ¹Kyung Hee University, ²NCD Co., Ltd., ³ETRI</p>
<p>FE1-D-2 09:15-09:30</p>	<p>Design Strategies to Implement a Highly-Reliable In₂O₃ Vertical Channel Transistor for 3-Dimensional Device Applications Chae-Eun Oh¹, Jong-Heon Yang², Chi-Sun Hwang², and Sung-Min Yoon¹ ¹Kyung Hee University, ²ETRI</p>
<p>FE1-D-3 09:30-09:45</p>	<p>Surface Treatment for High Performance, High Reliability In₂O₃ Thin-Film Transistors Jeong Eun Oh¹, Jae Young Lee², Nahyen Kim², and Jae Kyeong Jeong^{1,2} ¹Department of Electronics Engineering, University of Hanyang, ²Department of Artificial Intelligence Semiconductor Engineering, Hanyang University</p>
<p>FE1-D-4 09:45-10:00</p>	<p>SPICE-Compatible I-V Compact Model Considering Channel Length Effect in IGZO FETs Su Han Noh, Seung Joo Myoung, Dong Hyeop Shin, Sae Him Jung, Donguk Kim, Changwook Kim, Sung-Jin Choi, Jong-Ho Bae, Dong Myong Kim, and Dae Hwan Kim School of Electrical Engineering, Kookmin University</p>
<p>FE1-D-5 10:00-10:15</p>	<p>Electrical Performance and Hydrogen Permeability of Nitrogen-Doped PEALD-SiO_x Insulators Using N₂O Plasma in ALD-Oxide Semiconductor TFTs Tae-Heon Kim, Dong-Gyu Kim, and Jin-Seong Park Division of Materials Science and Engineering, Hanyang University</p>
<p>FE1-D-6 10:15-10:30</p>	<p>Strategical Dynamic Modulation of Turn-On Voltage for 2T0C DRAM Cell Introducing Charge-Trap Layer into Write Transistor Using IGZO Channel Kyung-Min Kim, Sang-Han Ko, and Sung-Min Yoon Kyung Hee University</p>



제 32회 한국반도체학술대회

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<p>FE1-D-7 10:30-10:45</p>	<p>Accurate Analysis of Halide Perovskite Field Effect Transistor Properties with Mobility Attenuation Effect Youngmin Song, Yeeun Kim, Sunggyu Ryoo, Jaeyong Woo, and Takhee Lee Department of Physics and Astronomy, Seoul National University</p>
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